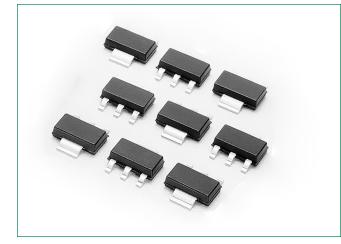


NYC222, NYC226, NYC228



Description

Designed and tested for repetitive peak operation required for CD ignition, fuel ignitors, flash circuits, motor controls and low-power switching applications.

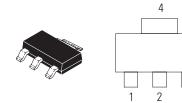
Features

- Blocking Voltage to 600 V
- High Surge Current 15 A
- Very Low Forward "On" Voltage at High Current
- Low-Cost Surface Mount SOT-223 Package

Po

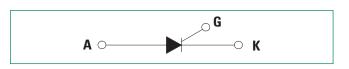
• These are Pb–Free Devices

Pin Out



3

Functional Diagram



Additional Information







Samples



Maximum Ratings ($T_1 = 25^{\circ}C$ unless otherwise noted)

- 0				
Rating		Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) $(R_{GK} = I_{K'}T_J - 40 \text{ to } +110^{\circ}C$, Sine Wave, 50 to 60 Hz)	V _{drm} , V _{rrm}	50 400 600	V	
On-State RMS Current (180° Conduction Angles; $T_c = 80^{\circ}C$)		I _{T (RMS)}	1.5	А
Average On-State Current, ($T_c = 65^{\circ}C$, f = 60 Hz, Time = 1 sec)		I _{T (AV)}	2.0	А
Peak Non-repetitive Surge Current, $@T_A = 25^{\circ}C$, (1/2 Cycle, Sine Wave, 60 Hz)	I _{TSM}	15	А	
Circuit Fusing Considerations (t = 8.3 ms)	l²t	0.9	A²s	
Forward Peak Gate Power (Pulse Width \leq 1.0 sec, $\rm T_{A}$ = 25°C)	P _{gM}	0.5	W	
Forward Average Gate Power (t = 8.3 msec, $T_A = 25^{\circ}$ C)	P _{G (AV)}	0.1	W	
Forward Peak Gate Current (Pulse Width \leq 1.0 s, T _A = 25°C)	I _{FGM}	0.2	A	
Reverse Peak Gate Voltage (Pulse Width \leq 1.0 µs, T _A = 25°C)	V _{RGM}	5.0	V	
Operating Junction Temperature Range @ Rated $V_{_{RRM}}$ and $V_{_{DRM}}$	Tj	-40 to +110	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

V_{press} for all spesses above the frequencies basis. Balance operating containing the frequencies in the continuous basis. Balance operating containing and V_{ress} for all spesses above, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics						
Rating	Symbol	Value	Unit			
Thermal Resistance, Junction-to-Ambient PCB Mounted	R _{eja}	156	mW			
Thermal Resistance, Junction–to–Tab Measured on MT2 Tab Adjacent to Epoxy	R _{eJT}	25	°C/W			
Maximum Device Temperature for Soldering Purposes for 10 Secs Maximum	TL	260	°C			

Electrical Characteristics · **OFF** ($T_c = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Мах	Unit
†Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	10	μA
$(V_{AK} = V_{DRM} = V_{RRM}; RGK = 1000 \Omega)$	T_ = 110°C	I	-	-	200	μA

Electrical Characteristics - **ON** ($T_{i} = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 2) ($I_{TM} = 2.2 \text{ A Peak}$)		V _{TM}	-	1.2	1.7	V
HGate Trigger Current (Note 3)	$T_c = 25^{\circ}C$		_	30	200	
$(V_{AK} = 7 V, R_{L} = 100 \Omega)$	$T_c = -40^{\circ}C$	GT	_	_	500	μA
Gate Trigger Voltage (dc) (Note 3)	$T_c = 25^{\circ}C$		-	-	0.8	
$(V_{AK} = 7 \text{ Vdc}, \text{ R}_{L} = 100\Omega)$	$T_c = -40^{\circ}C$	V_{GT}	-	-	1.2	V
Gate Non-Trigger Voltage ($V_{AK} = V_{DRM'} R_{L} = 100 \Omega$)	$T_c = 110^{\circ}C$	V _{gd}	0.1	_	-	V
Holding Current	$T_c = 25^{\circ}C$		_	2.0	5.0	
$(V_{AK} = 12 \text{ V}, \text{ R}_{GK} = 1000 \Omega)$ Initiating Current = 200 mA	$T_c = -40^{\circ}C$		_	_	10	mA



Dynamic Characteristics						
Characteristic	Symbol	Min	Тур	Мах	Unit	
Critical Rate-of-Rise of Off State Voltage ($T_c = 110^{\circ}C$)	dv/dt	-	25	-	V/µs	
Critical Rate of Rise of On–State Current $(T_c = 110^{\circ}C, I_g = 2 \times I_{gT'} R_{GK} = 1 \text{ k}\Omega)$	di/dt	-	20	_	A/µs	

2. Pulse Width =1.0 ms, Duty Cycle \leq 1%. 3. RGK Current not included in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{drm}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

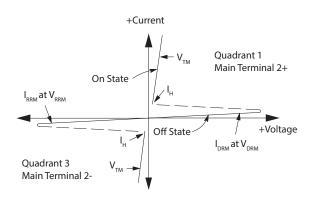
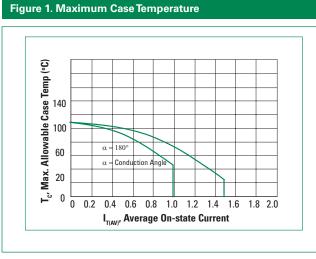




Figure 3. Typical Forward Voltage

Current Derating



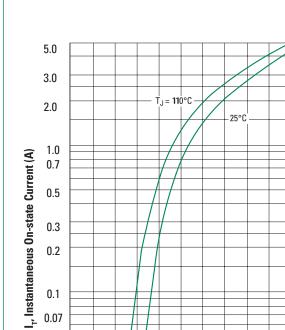
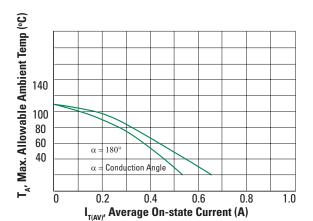


Figure 2. Maximum Ambient Temperature



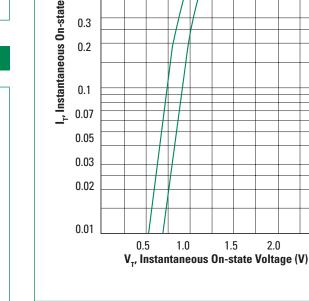
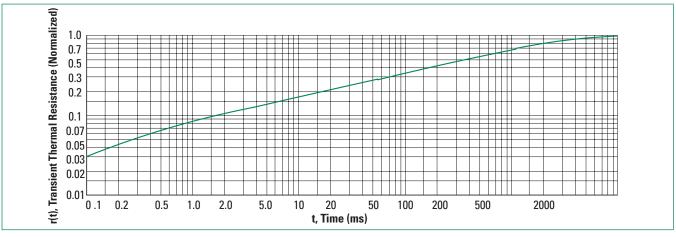


Figure 4. Thermal Response



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2.5



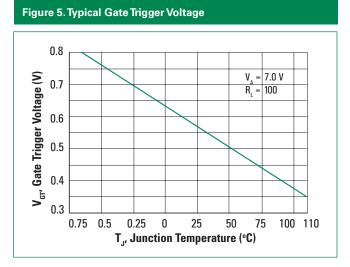


Figure 7. Typical Holding Current

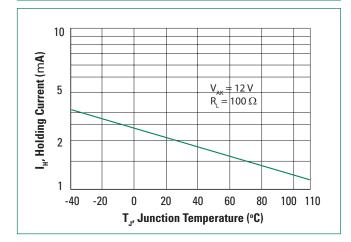


Figure 6. Typical Gate Trigger Current

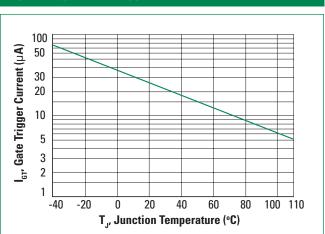
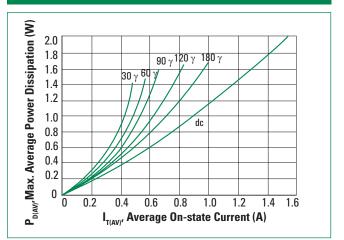
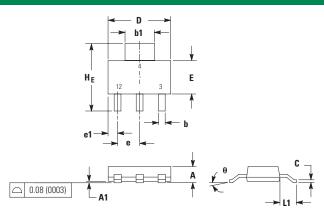


Figure 8. Power Dissipation



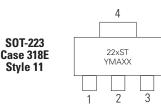


Dimensions



Part Marking System



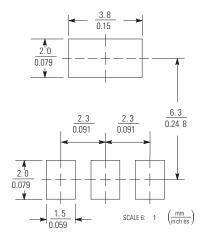




XX =Lot Serial Code

Dim		Millimeters				
Dim	Min	Nom	Max	Min	Nom	Мах
Α			0.071			1.80
A1	0.001	0.003	0.005	0.02	0.07	0.13
b	0.026	0.030	0.033	0.66	0.75	0.84
b1	0.114	0.118	0.122	2.90	3.00	3.10
С	0.009	0.011	0.014	0.23	0.29	0.35
D	0.260	0.260	0.264	6.60	6.60	6.71
Е	0.130	0.138	0.146	3.30	3.50	3.70
е		0.091			2.30	
e1	0.030	0.037	0.045	0.75	0.95	1.15
L1	0.059	0.069	0.079	1.50	1.75	2.00
HE	0.264	0.276	0.287	6.70	7.00	7.30
ø	0°		10°	0°		10°

Soldering Footprint



1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

Pin Assignment				
1	K (Cathode)			
2	A (Anode)			
3	Gate			
4	4 A (Anode)			

Ordering Information						
Device	Package	Shipping				
NYC222STT1G	SOT-223 (Pb-Free)	1000/Tape & Reel				
NYC226STT1G	SOT-223 (Pb-Free)					
NYC228STT1G	SOT-223 (Pb-Free)					

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